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# High Purity Silicon 9

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**Sponsoring Division:**

**Electronics and Photonics**



Published by  
**The Electrochemical Society**  
65 South Main Street, Building D  
Pennington, NJ 08534-2839, USA  
tel 609 737 1902  
fax 609 737 2743  
[www.electrochem.org](http://www.electrochem.org)

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**ecstransactions™**

**Vol. 3 No. 4**

**ISBN 1-56677-504-3**

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Published by:  
The Electrochemical Society, Inc.  
65 South Main Street  
Pennington, New Jersey 08534-2839, USA  
Telephone 609.737.1902  
Fax 609.737.2743  
e-mail: [ecs@electrochem.org](mailto:ecs@electrochem.org)  
Web: [www.electrochem.org](http://www.electrochem.org)

ISBN 1-56677-504-3

Printed in the United States of America

**ECS Transactions, Volume 3, Issue 4**  
High Purity Silicon 9

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